

20V N-Channel Power MOSFET



SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

Note:

MSL 1 (Moisture Sensitivity Level) per J-STD-020

Key Parameter Performance

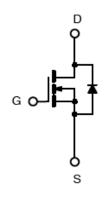
Parameter		Value	Unit	
V_{DS}		20	V	
R _{DS(on)} (max)	$V_{GS} = 4.5V$	21		
	$V_{GS} = 2.5V$	25	mΩ	
	$V_{GS} = 1.8V$	32		
Q_g		5.8	nC	

Ordering Information

Ordering code	Package	Packing
TSM210N02CX RFG	SOT-23	3kpcs / 7" Reel
	·	

Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	20	V
Gate-Source Voltage		V _{GS}	V _{GS} ±10	
Continuous Drain Current	T _C = 25°C	I _D	6.7	Α
	T _C = 100°C		4.2	Α
Pulsed Drain Current (Note 1)		I _{DM}	26.8	Α
Power Dissipation @ T _C = 25°C		P _D	1.56	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	80	°C/W



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Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	20			V
	$V_{GS} = 4.5V, I_D = 4A$			19	21	
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 3A$	R _{DS(ON)}		22	25	mΩ
	$V_{GS} = 1.8V, I_D = 2A$			26	32	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	0.3	0.6	0.8	V
	$V_{DS} = 20V, V_{GS} = 0V$	· · ·			1	μΑ
Zero Gate Voltage Drain Current	V _{DS} = 16V, T _J = 125°C	I _{DSS}			10	
Gate Body Leakage	$V_{GS} = \pm 10V, V_{DS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance (Note 2)	$V_{DS} = 10V, I_{S} = 4A$	g _{fs}		9.5		S
Dynamic						
Total Gate Charge (Note 2,3)		Q_g		5.8		nC
Gate-Source Charge (Note 2,3)	$V_{DS} = 10V, I_{D} = 4A,$	Q_gs		0.6		
Gate-Drain Charge (Note 2,3)	$V_{GS} = 4.5V$	Q_gd		2		
Input Capacitance		C _{iss}		600		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	C _{oss}		70		pF
Reverse Transfer Capacitance	- f = 1.0MHz	C _{rss}		45		•
Switching						
Turn-On Delay Time (Note 2,3)		t _{d(on)}		5.0		
Turn-On Rise Time (Note 2,3)	$V_{DD} = 10V, I_D = 1A,$	t _r		14.4		
Turn-Off Delay Time (Note 2,3)	$V_{GS} = 4.5V, R_{GEN} = 25\Omega$	t _{d(off)}		30.0		ns
Turn-Off Fall Time (Note 2,3)		t _f		9.2		
Source-Drain Diode Ratings and Ch	aracteristic				1	
Maximum Continuous Drain-Source					0.7	_
Diode Forward Current	Integral reverse diode in the MOSFET	I _S			6.7	Α
Maximum Pulse Drain-Source Diode		I _{SM}	-		26.8	Α
Forward Current						
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V_{SD}			1	V

Note:

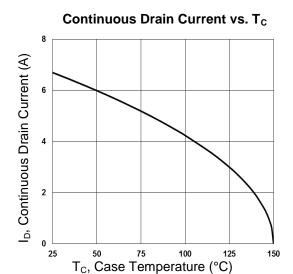
- 1. Pulse width limited by safe operating area
- 2. Pulse test: pulse width ≤ 300µs, duty cycle ≤ 2%
- 3. Switching time is essentially independent of operating temperature.



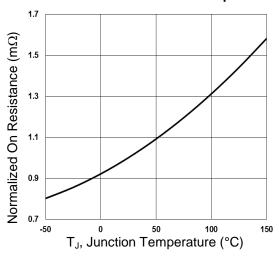
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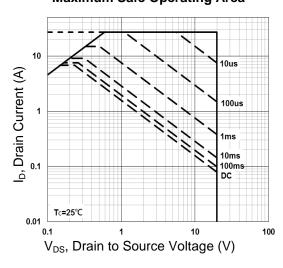
Electrical Characteristics Curve



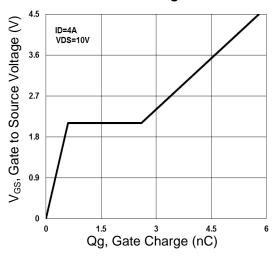
On-Resistance vs. Junction Temperature



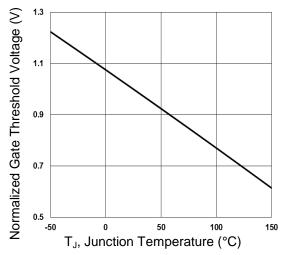
Maximum Safe Operating Area



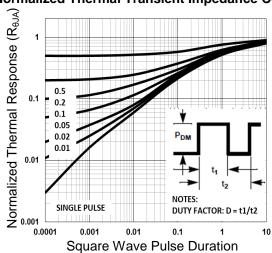
Gate Charge



Threshold Voltage vs. Junction Temperature



Normalized Thermal Transient Impedance Curve

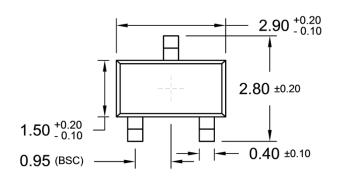


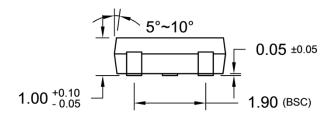


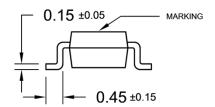
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SOT-23 Mechanical Drawing

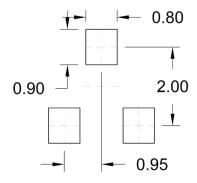






Unit: Millimeters

SUGGESTED PAD LAYOUT (Unit: Millimeters)



Marking Diagram



21 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

4/5

L = Lot Code

Version: B1811



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TSM210N02CX 20V N-Channel Power MOSFET

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